

NPN SILICON RF TRANSISTOR

DESCRIPTION:

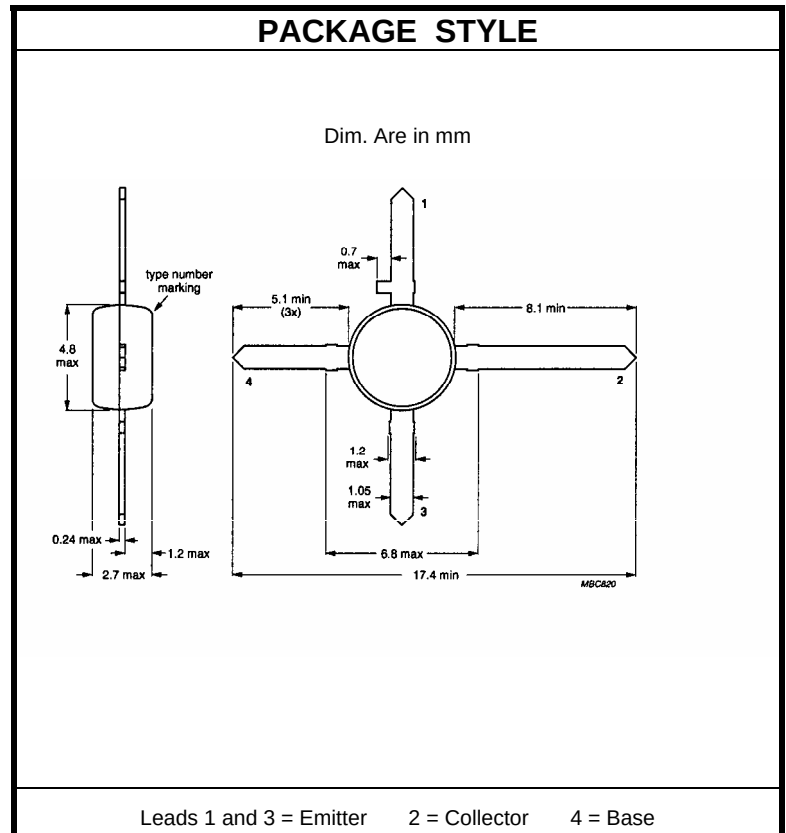
The **MRF581** is Designed for
High current low Power Amplifier
Applications up to 1.0 GHz.

FEATURES:

- Low Noise Figure
- Low Intermodulation Distortion
- High Gain
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	2.5 V
P_{DISS}	2.5 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0\text{ mA}$		36			V
BV_{CEO}	$I_C = 1.0\text{ mA}$		18			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$		2.5			V
I_{EBO}	$V_{EB} = 2.0\text{ V}$				100	μA
I_{CBO}	$V_{CB} = 15\text{ V}$				100	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 50\text{ mA}$		50		200	---
C_{cb}	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$			1.4	2.0	pF
G_P	$V_{CC} = 10\text{ V}$ $I_C = 50$ $f = 0.5\text{ GHz}$		13	15.5		dB